

# NTR4101P, NTRV4101P

## Trench Power MOSFET –20 V, Single P–Channel, SOT–23

### Features

- Leading –20 V Trench for Low  $R_{DS(on)}$
- –1.8 V Rated for Low Voltage Gate Drive
- SOT–23 Surface Mount for Small Footprint
- AEC Q101 Qualified – NTRV4101P
- These Devices are Pb–Free and are RoHS Compliant

### Applications

- Load/Power Management for Portables
- Load/Power Management for Computing
- Charging Circuits and Battery Protection

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain–to–Source Voltage		$V_{DSS}$	–20	V	
Gate–to–Source Voltage		$V_{GS}$	$\pm 8.0$	V	
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	$I_D$	–2.4	A
				$T_A = 85^\circ\text{C}$	
	$t \leq 10\text{ s}$	$T_A = 25^\circ\text{C}$	–3.2		
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	$P_D$	0.73	W
				$t \leq 10\text{ s}$	
Continuous Drain Current (Note 2)	Steady State	$T_A = 25^\circ\text{C}$	$I_D$	–1.8	A
		$T_A = 85^\circ\text{C}$		–1.3	
Power Dissipation (Note 2)		$T_A = 25^\circ\text{C}$	$P_D$	0.42	W
Pulsed Drain Current	$tp = 10\ \mu\text{s}$	$I_{DM}$	–18	A	
ESD Capability (Note 3)	$C = 100\ \text{pF}$ , $RS = 1500\ \Omega$	ESD	225	V	
Operating Junction and Storage Temperature		$T_J$ , $T_{STG}$	–55 to 150	$^\circ\text{C}$	
Source Current (Body Diode)		$I_S$	–2.4	A	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		$T_L$	260	$^\circ\text{C}$	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction–to–Ambient – Steady State (Note 1)	$R_{\theta JA}$	170	$^\circ\text{C}/\text{W}$
Junction–to–Ambient – $t < 10\text{ s}$ (Note 1)	$R_{\theta JA}$	100	
Junction–to–Ambient – Steady State (Note 2)	$R_{\theta JA}$	300	

1. Surface–mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces)
2. Surface–mounted on FR4 board using the minimum recommended pad size.
3. ESD Rating Information: HBM Class 0

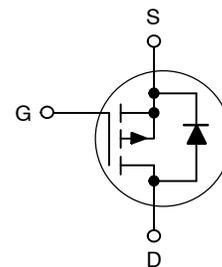


**ON Semiconductor®**

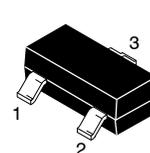
<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(ON)}$ TYP	$I_D$ MAX
–20 V	70 m $\Omega$ @ –4.5 V	–3.2 A
	90 m $\Omega$ @ –2.5 V	
	112 m $\Omega$ @ –1.8 V	

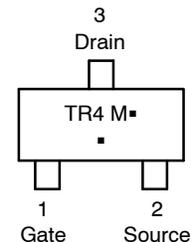
### P–Channel MOSFET



### MARKING DIAGRAM & PIN ASSIGNMENT



**SOT–23  
CASE 318  
STYLE 21**



TR4 = Device Code  
M = Date Code  
▪ = Pb–Free Package

(\*Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping†
NTR4101PT1G	SOT–23 Pb–Free	3000 / Tape & Reel
NTRV4101PT1G	SOT–23 Pb–Free	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NTR4101P, NTRV4101P

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage (Note 4) ( $V_{GS} = 0\text{ V}$ , $I_D = -250\ \mu\text{A}$ )	$V_{(BR)DSS}$	-20			V
Zero Gate Voltage Drain Current (Note 4) ( $V_{GS} = 0\text{ V}$ , $V_{DS} = -16\text{ V}$ )	$I_{DSS}$			-1.0	$\mu\text{A}$
Gate-to-Source Leakage Current ( $V_{GS} = \pm 8.0\text{ V}$ , $V_{DS} = 0\text{ V}$ )	$I_{GSS}$			$\pm 100$	nA

### ON CHARACTERISTICS

Gate Threshold Voltage (Note 4) ( $V_{GS} = V_{DS}$ , $I_D = -250\ \mu\text{A}$ )	$V_{GS(th)}$	-0.4	-0.72	-1.2	V
Drain-to-Source On-Resistance ( $V_{GS} = -4.5\text{ V}$ , $I_D = -1.6\text{ A}$ ) ( $V_{GS} = -2.5\text{ V}$ , $I_D = -1.3\text{ A}$ ) ( $V_{GS} = -1.8\text{ V}$ , $I_D = -0.9\text{ A}$ )	$R_{DS(on)}$		70 90 112	85 120 210	$\text{m}\Omega$
Forward Transconductance ( $V_{DS} = -5.0\text{ V}$ , $I_D = -2.3\text{ A}$ )	$g_{FS}$		7.5		S

### CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	$(V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = -10\text{ V})$	$C_{iss}$	675		pF
Output Capacitance		$C_{oss}$	100		
Reverse Transfer Capacitance		$C_{rss}$	75		
Total Gate Charge	$(V_{GS} = -4.5\text{ V}, V_{DS} = -10\text{ V}, I_D = -1.6\text{ A})$	$Q_{G(tot)}$	7.5	8.5	nC
Gate-to-Source Gate Charge	$(V_{DS} = -10\text{ V}, I_D = -1.6\text{ A})$	$Q_{GS}$	1.2		nC
Gate-to-Drain "Miller" Charge	$(V_{DS} = -10\text{ V}, I_D = -1.6\text{ A})$	$Q_{GD}$	2.2		nC
Gate Resistance		$R_G$	6.5		$\Omega$

### SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	$(V_{GS} = -4.5\text{ V}, V_{DS} = -10\text{ V}, I_D = -1.6\text{ A}, R_G = 6.0\ \Omega)$	$t_{d(on)}$	7.5		ns
Rise Time		$t_r$	12.6		
Turn-Off Delay Time		$t_{d(off)}$	30.2		
Fall Time		$t_f$	21.0		

### DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	$(V_{GS} = 0\text{ V}, I_S = -2.4\text{ A})$	$V_{SD}$	-0.82	-1.2	V
Reverse Recovery Time	$(V_{GS} = 0\text{ V}, dI_{SD}/dt = 100\text{ A}/\mu\text{s}, I_S = -1.6\text{ A})$	$t_{rr}$	12.8	15	ns
Charge Time		$t_a$	9.9		ns
Discharge Time		$t_b$	3.0		ns
Reverse Recovery Charge		$Q_{rr}$	1008		nC

4. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
5. Switching characteristics are independent of operating junction temperature.

# NTR4101P, NTRV4101P

## TYPICAL PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

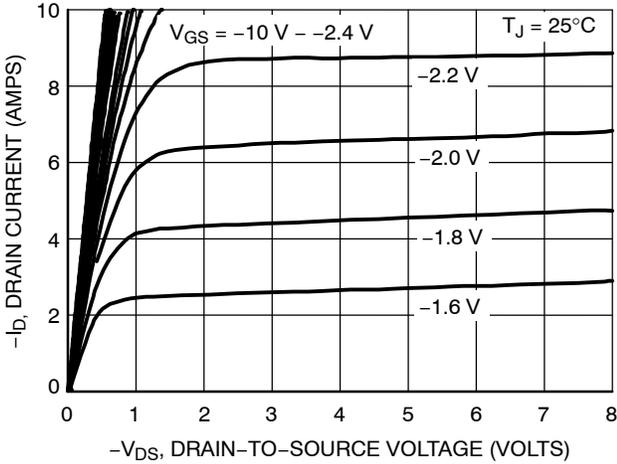


Figure 1. On-Region Characteristics

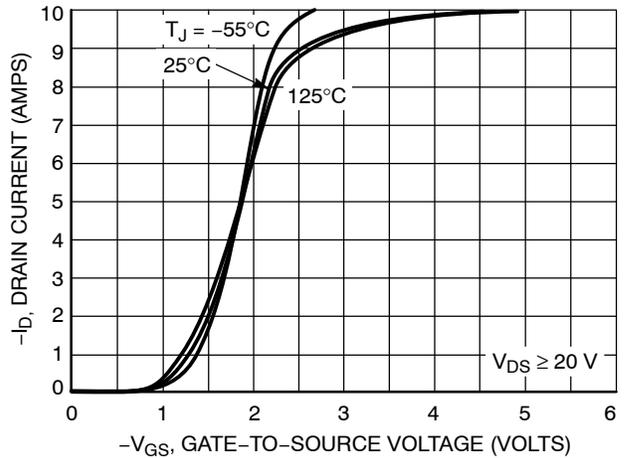


Figure 2. Transfer Characteristics

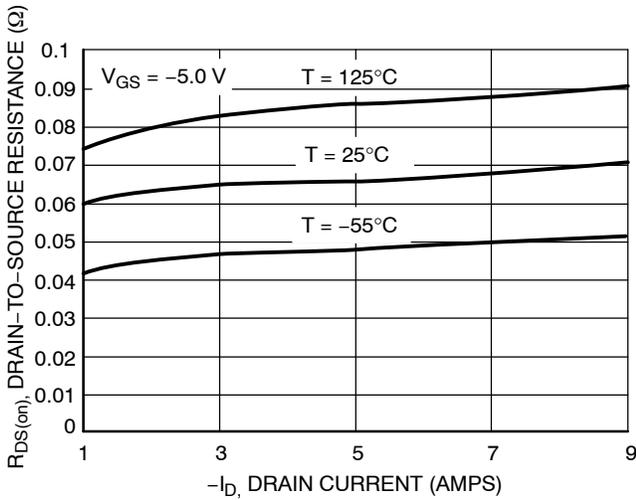


Figure 3. On-Resistance vs. Drain Current and Temperature

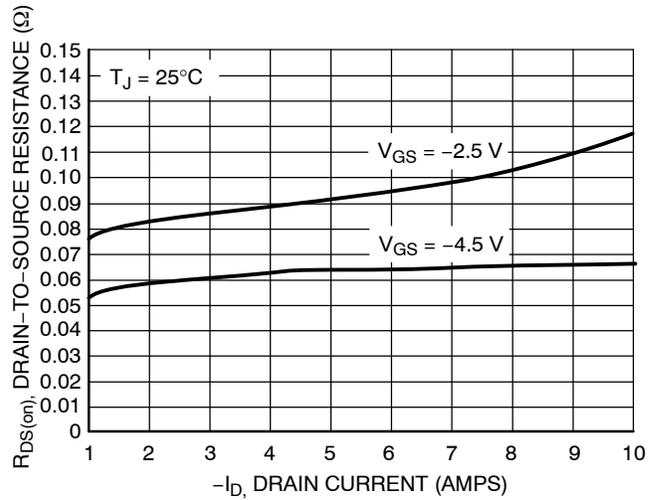


Figure 4. On-Resistance vs. Drain Current and Temperature

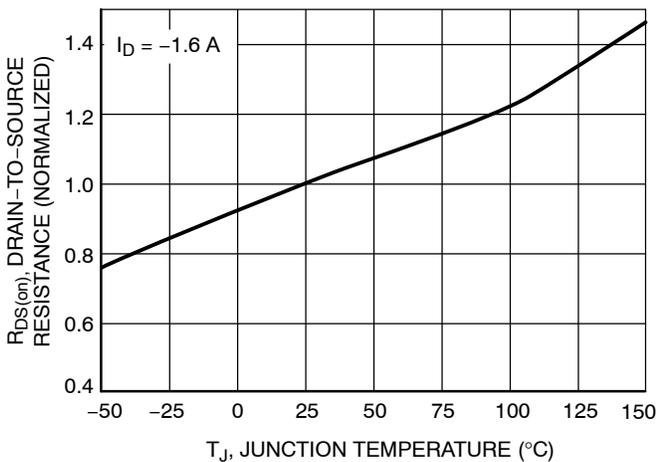


Figure 5. On-Resistance Variation with Temperature

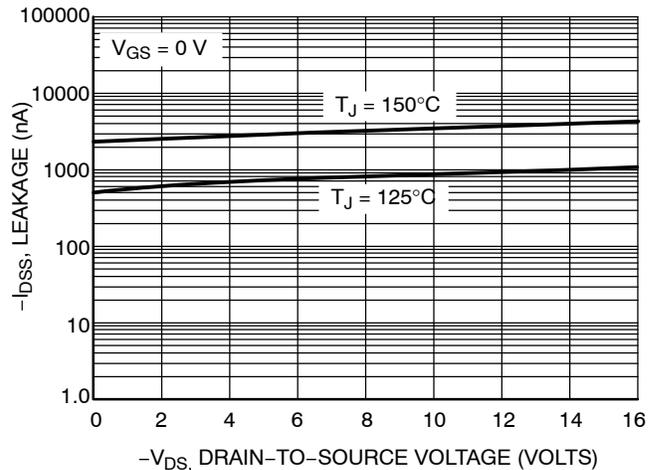


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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## TYPICAL PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

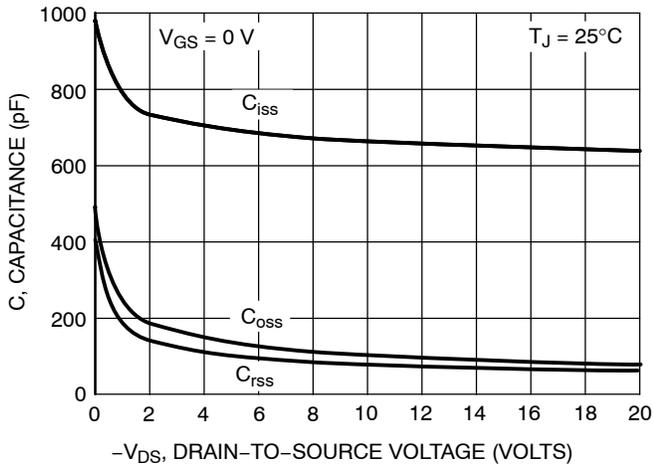


Figure 7. Capacitance Variation

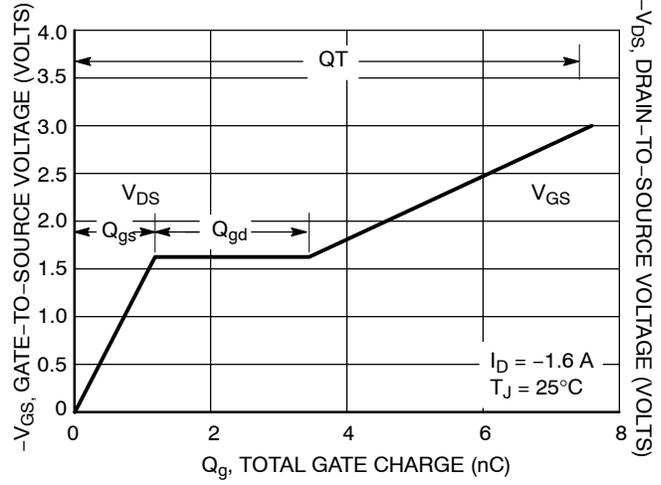


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Gate Charge

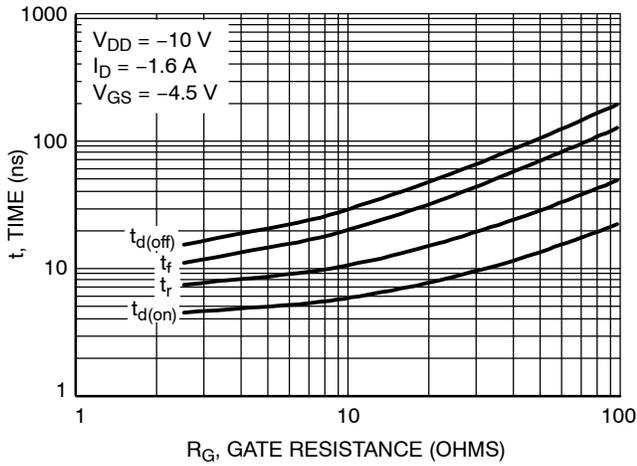


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

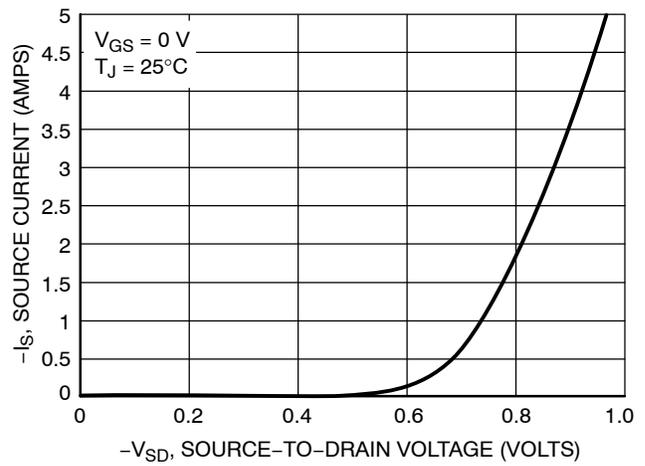
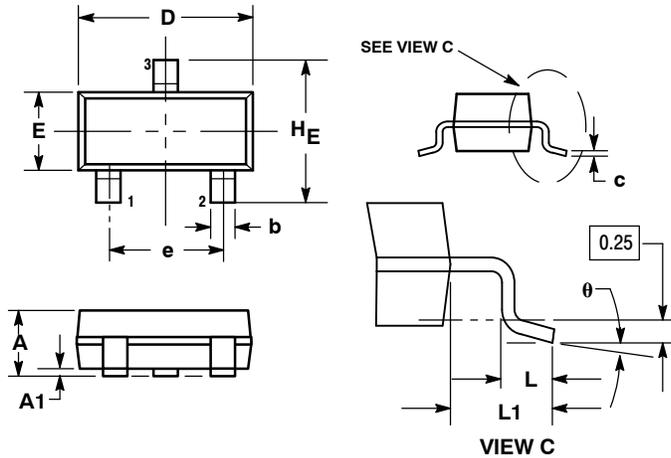


Figure 10. Diode Forward Voltage vs. Current

# NTR4101P, NTRV4101P

## PACKAGE DIMENSIONS

SOT-23 (TO-236)  
CASE 318-08  
ISSUE AP



NOTES:

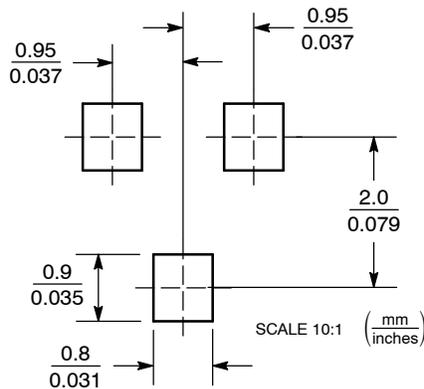
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

STYLE 12:

- PIN 1. CATHODE
- CATHODE
- ANODE

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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